

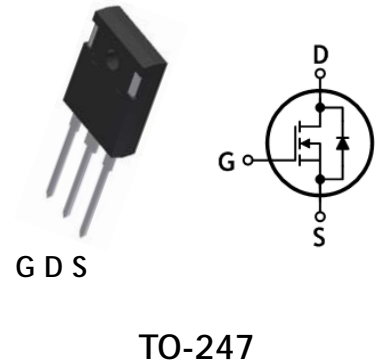
## SWITCHING REGULATOR APPLICATION

### Features

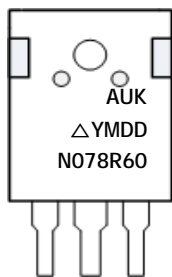
- 600V Super-junction MOSFET
- Low FOM  $R_{DS(on)} * Q_g$
- Low drain-source On-resistance:  $R_{DS(on)}=78m\Omega$  (Max.)
- 100% avalanche tested
- RoHS compliant device

### Ordering Information

Part Number	Marking	Package
SJMN078R60W	N078R60	TO-247



### Marking Information



- Column 1: Manufacturer  
Column 2: Production Information  
e.g.)  $\Delta$ YMDD  
-.  $\Delta$ : Factory Management Code  
-. YMDD: Date Code (Year, Month, Daily)  
Column 3: Device Code

### Absolute maximum ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	600	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_c=25^\circ\text{C}$	48	A
		$T_c=100^\circ\text{C}$	28	A
Drain current (Pulsed) *	$I_{DM}$	144	A	
Single pulsed avalanche energy <sup>(Note 2)</sup>	$E_{AS}$	1508	mJ	
Repetitive avalanche current <sup>(Note 1)</sup>	$I_{AR}$	9.6	A	
Repetitive avalanche energy <sup>(Note 1)</sup>	$E_{AR}$	41.7	mJ	
Power dissipation	$P_D$	417	W	
Junction temperature	$T_J$	150	$^\circ\text{C}$	
Storage temperature range	$T_{stg}$	-55~150	$^\circ\text{C}$	

\* Limited only maximum junction temperature

## Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 0.3	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 40	

## Electrical Characteristics ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ , $V_{DS}=V_{GS}$	2.5	-	4.5	V
Drain-source cut-off current	$I_{DSS}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ , $I_D=24\text{A}$	-	66	78	m $\Omega$
Forward transfer conductance (Note 4)	$g_{fs}$	$V_{DS}=30\text{V}$ , $I_D=24\text{A}$	-	45	-	S
Input capacitance	$C_{iss}$	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	5234	-	pF
Output capacitance	$C_{oss}$		-	3918	-	
Reverse transfer capacitance	$C_{rss}$		-	43	-	
Turn-on delay time (Note 4,5)	$t_{d(on)}$	$V_{DD}=300\text{V}$ , $I_D=48\text{A}$ , $R_G=25\Omega$ , $V_{GS}=10\text{V}$	-	82	-	ns
Rise time (Note 4,5)	$t_r$		-	186	-	
Turn-off delay time (Note 4,5)	$t_{d(off)}$		-	352	-	
Fall time (Note 4,5)	$t_f$		-	111	-	
Total gate charge (Note 4,5)	$Q_g$	$V_{DS}=480\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=48\text{A}$	-	131	-	nC
Gate-source charge (Note 4,5)	$Q_{gs}$		-	24	-	
Gate-drain charge (Note 4,5)	$Q_{gd}$		-	58	-	

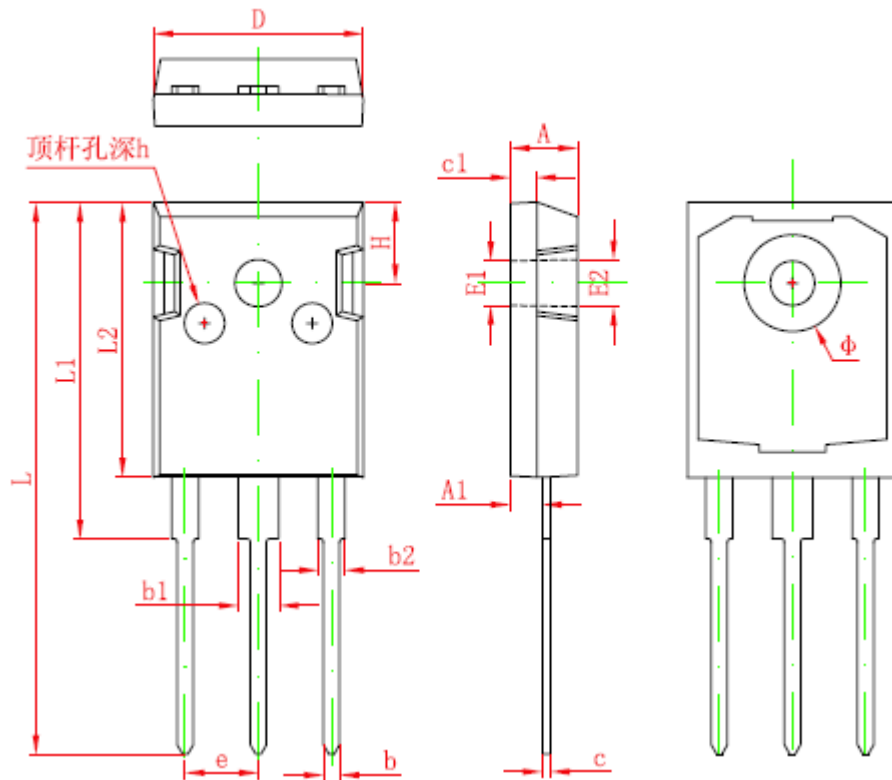
## Source-Drain Diode Ratings and Characteristics ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	48	A
Source current (Pulsed)	$I_{SM}$		-	-	144	A
Forward voltage	$V_{SD}$	$V_{GS}=0\text{V}$ , $I_S=48\text{A}$	-	-	1.25	V
Reverse recovery time (Note 4,5)	$t_{rr}$	$I_S=48\text{A}$ , $V_{GS}=0\text{V}$ $di_S/dt=100\text{A}/\mu\text{s}$	-	654	-	ns
Reverse recovery charge (Note 4,5)	$Q_{rr}$		-	14.7	-	$\mu\text{C}$

Note:

1. Repeated rating: Pulse width limited by safe operating area
2.  $I_{AS}=9.6\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , starting  $T_J=25^\circ\text{C}$ , not subject to production test - verified by design/characterization
3. Pulse test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
4. Essentially independent of operating temperature typical characteristics

Package Outline Dimensions (Unit: mm)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012

The AUK Corp. products are intended for the use as components in general electronic equipment (Office and communication equipment, measuring equipment, home appliance, etc.).

Please make sure that you consult with us before you use these AUK Corp. products in equipments which require high quality and / or reliability, and in equipments which could have major impact to the welfare of human life(atomic energy control, airplane, spaceship, transportation, combustion control, all types of safety device, etc.). AUK Corp. cannot accept liability to any damage which may occur in case these AUK Corp. products were used in the mentioned equipments without prior consultation with AUK Corp..

Specifications mentioned in this publication are subject to change without notice.